

AMENDMENTS TO THE CLAIMS:

Claims 5-11 are canceled without prejudice or disclaimer.

1. (Currently amended) A group III nitride compound semiconductor light-emitting device comprising:
 - a semiconductor laminate portion including ~~containing~~ a light-emitting layer; and
 - a groove formed in said semiconductor laminate portion so as to extend from a light emission observation surface of said semiconductor laminate portion to reach at least said light-emitting layer; and
 - a p-type electrode and an n-type electrode formed in a same surface side of said semiconductor laminate portion,
 - wherein said semiconductor laminate portion is partitioned into a plurality of blocks by said groove,
 - wherein an auxiliary electrode is provided so as to extend from said p-type electrode such that a current from said p-type electrode is supplied to each of said plurality of blocks, and
 - wherein an electrically insulating layer is formed between said auxiliary electrode and said semiconductor laminate portion.
2. (Currently amended) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said groove is distributed substantially equally in said light emission observation surface.

3. (Original) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said groove is formed by etching.
4. (Original) A group III nitride compound semiconductor light-emitting device according to claim 3, wherein an n-type seat electrode-forming surface is provided at a level equal to a bottom of said groove.
- 5-11. (Canceled).
12. (New) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said groove includes an opening portion formed in said light emission observation surface, and
wherein said groove reveals a side surface of said light-emitting layer.
13. (New) A group III nitride compound semiconductor light-emitting device according to claim 12, wherein said groove includes a circumferential wall; and
wherein light emitted from the revealed portion of said side surface of said light-emitting layer into said groove is reflected by a portion of said circumferential wall of said groove out of the opening portion of said groove toward an outside of said groove.
14. (New) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein a width of said groove is in a range of from 0.5 to 30 μm , and preferably said

width of said groove is in a range of from 1 to 25 μm , and more preferably, said width of said groove is in a range of from 1.5 to 20 μm , and more preferably, said width of said groove is in a range of from 2 to 15 μm .

15. (New) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said groove comprises a V-shaped groove.

16. (New) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein a width of said groove is distributed substantially unequally in said light emission observation surface.

17. (New) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein each of said plurality of blocks include a light-emitting region revealed on a side surface thereof.

18. (New) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said semiconductor laminate portion includes a plurality of current diffusion paths formed between said p-type seat electrode and said n-type seat electrode,

wherein each of said plurality of current diffusion paths are divided by said groove, and

wherein each of said plurality of current diffusion paths includes a substantially same length and a substantially same width.

19. (New) A group III nitride compound semiconductor light-emitting device according to claim 1, further comprising:

an n-type seat electrode-forming surface formed in said semiconductor laminate portion and adapted to mount said n-type seat electrode,

wherein a bottom surface of said groove is located substantially at a same height as said n-type seat electrode-forming surface.

20. (New) A group III nitride compound semiconductor light-emitting device comprising:

a semiconductor laminate portion including a light-emitting layer;

a groove formed in said semiconductor laminate portion; and

a p-type electrode and an n-type electrode formed in a same surface side of said semiconductor laminate portion,

wherein said groove extends from an opening in a light emission observation surface of said semiconductor laminate portion into said semiconductor laminate portion to reach at least said light-emitting layer,

wherein said groove reveals a side surface of said light-emitting layer,

wherein said semiconductor laminate portion is partitioned into a plurality of blocks by said groove,

wherein an auxiliary electrode is provided so as to extend from said p-type electrode such that a current from said p-type electrode is supplied to each of said plurality of blocks, and

wherein an electrically insulating layer is formed between said auxiliary electrode and said semiconductor laminate portion.

21. (New) A group III nitride compound semiconductor light-emitting device according to claim 20, wherein said groove includes a circumferential wall; and

wherein light emitted from the revealed portion of said side surface of said light-emitting layer into said groove is reflected by a portion of said circumferential wall of said groove out of the opening portion of said groove toward an outside of said groove.